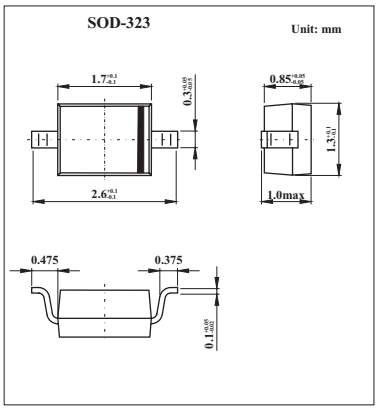
Schottky barrier diode

1PS76SB10



Features

- Low forward volatge
- Guard ring protected
- Very small plastic SMD package.

Absolute Maximum Ratings Ta = 25℃

PARAMATER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	V_R			30	V
continuous forward current	V_F			200	mA
repetitive peak forward current	T_{FRM}	tp ≤ 1 s; δ≤ 0.5		300	mA
non-reetitiive peak forward current	T_{FSM}	tp < 10 ms		600	mA
storage temperature	T_{stg}		-65	+150	℃
junction temperature	T_j			125	℃
operating ambient temperature	T_{amb}		-65	+125	℃

Electrical Characteristics Ta = 25℃

PARAMATER	SYMBOL	CONDITIONS	MAX	UNIT
forward volatge	V_F	I_F = 0.1 mA	240	mV
		I_F = 1 mA	320	
		I_F = 10 mA	400	
		I_F = 30 mA	500	
		I_F = 100 mA	800	
reverse current	I_R	V_R = 25 V; note 1;	2	μA
diode capacitance	C_d	f = 1 MHz; V_R = 1V;	10	pF

Note

1. Pulsed test: tp = 300 μs; δ = 0.02.

Marking

Marking	S0